

EAST: [04/3810 latch for sram.wsp:1]

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Default operator: GR

39 and 41

June 2004

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|---|---|---------------|------------|--------|---|--|---------|-----------|---------|-----------|---|---|---|-------|-----|-----------|--|
| 1 | | Koga, Tsuyos | US 2004003 | 20040 | 1 | Semiconductor memory device | 365/189 | 365/149 | | | | | | | | US 200400 | |
| 2 | | Gonzalez, Fer | US 6281276 | 20010 | 1 | Cross coupled thin film transistors and static | 438/159 | 257/E27.1 | | | | | | | | US 628127 | |
| 3 | | Gonzalez, Fer | US 6054742 | 20000 | 1 | Structure for cross coupled thin film transist | 257/392 | 257/359 | | | | | | | | US 605474 | |
| 4 | | Gonzalez, Fer | US 5640342 | 19970 | 1 | Structure for cross coupled thin film transist | 365/156 | 257/903 | | | | | | | | US 564034 | |
| 5 | | Gonzalez, Fer | US 5572461 | 18961 | 1 | Static random access memory cell having a c | 365/156 | 257/385 | | | | | | | | US 557246 | |
| 6 | | Manning, Mo | US 5422499 | 19950 | 1 | Sixteen megabit static random access memo | 257/87 | 257/89 | | | | | | | | US 542249 | |
| 7 | | DeJong, Jan | US 5359226 | 18841 | 1 | Static memory with self aligned contacts an | 257/773 | 257/393 | | | | | | | | US 535922 | |
| 8 | | GONZALEZ, F | US 5572461 | 19961 | 1 | Silicon@ substrate based SRAM having max. | | | | | | | | | | US 557246 | |